## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1 kV
- Ultra thin package profile with 0.37 mm height

## 3. Applications

- Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-50	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-230	mA
Static charac	teristics			•			
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -10 V; $I_D$ = -100 mA; $T_j$ = 25 °C		-	4.5	7.5	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



50 V, single P-channel Trench MOSFET

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D
2	S	source		
3	D	drain	Transparent top view  DFN1006B-3 (SOT883B)	G S 017aaa259

# 6. Ordering information

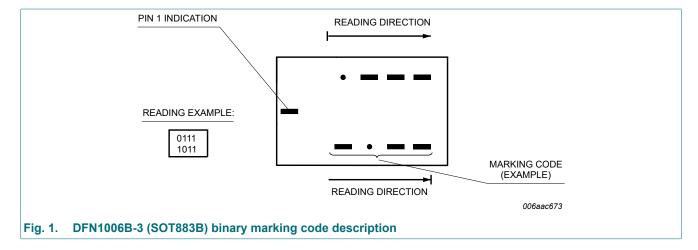
**Table 3. Ordering information** 

Type number	Package						
	Name	Description	Version				
BSS84AKMB	DFN1006B-3	plastic, leadless ultra small plastic package; 3 solder lands; 0.35 mm pitch; 1.0 mm x 0.6 mm x 0.37 mm body	SOT883B				

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BSS84AKMB	0000 0010



# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-50	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-230	mA
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	[1]	-	-150	mA
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	-0.9	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T <sub>sp</sub> = 25 °C		-	2700	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode		'	1		
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-230	mA
ESD maximi	um rating		'	'	,	
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	1000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

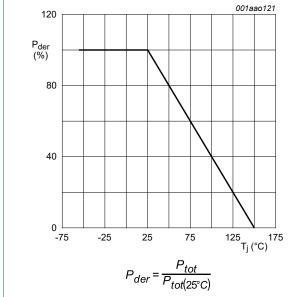


Fig. 2. Normalized total power dissipation as a function of junction temperature

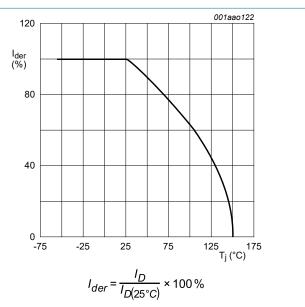
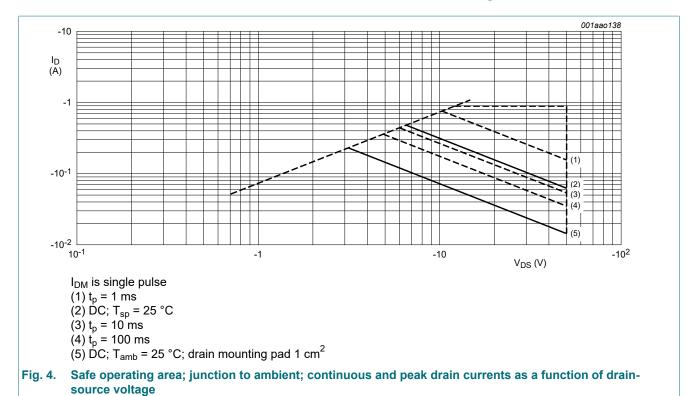


Fig. 3. Normalized continuous drain current as a function of junction temperature

## 50 V, single P-channel Trench MOSFET



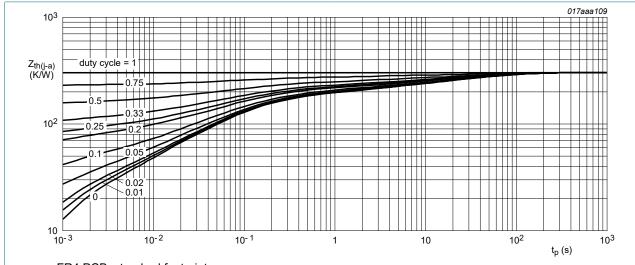
#### 50 V, single P-channel Trench MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

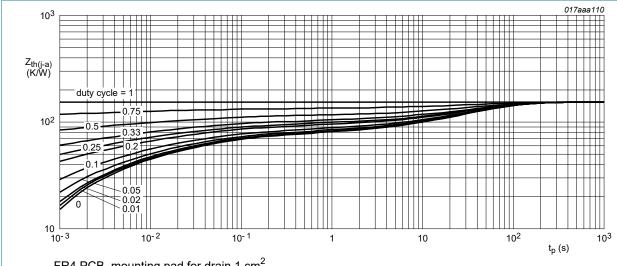
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	305	350	K/W
junction to ambient	junction to ambient		[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	40	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1  $\mathrm{cm}^2$ 

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, single P-channel Trench MOSFET

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	-				
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-50	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1.1	-1.6	-2.1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -50 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>DS</sub> = -50 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-2	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -10 V; $I_D$ = -100 mA; $T_j$ = 25 °C	-	4.5	7.5	Ω
	resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -100 mA; T <sub>j</sub> = 150 °C	-	8	13.5	Ω
		$V_{GS} = -5 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	5.7	8.5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	150	-	mS
Dynamic ch	aracteristics		•			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -25 \text{ V}; I_D = -200 \text{ mA}; V_{GS} = -5 \text{ V};$	-	0.26	0.35	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge	$V_{DS}$ = -10 V; $I_D$ = -200 mA; $V_{GS}$ = -5 V; $T_j$ = 25 °C	-	0.09	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -25 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	24	36	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	4.5	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -30 \text{ V}; R_L = 250 \Omega; V_{GS} = -10 \text{ V};$	-	13	26	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	48	96	ns
t <sub>f</sub>	fall time	]	-	25	-	ns
Source-drai	in diode		'	,	,	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = -115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-0.48	-0.85	-1.2	V

### 50 V, single P-channel Trench MOSFET

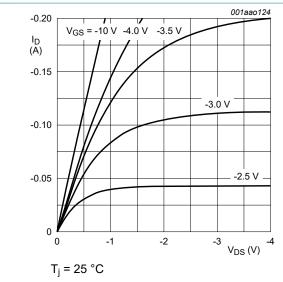
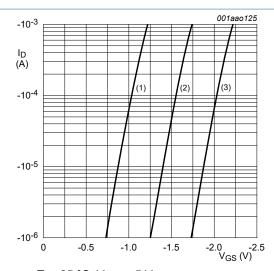


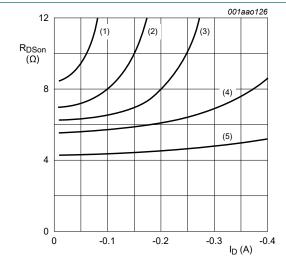
Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25 \,^{\circ}C$ 

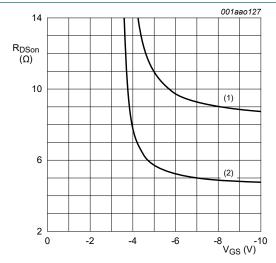
 $(1) V_{GS} = -3.0 V$ 

 $(2) V_{GS} = -3.5 V$ 

(3)  $V_{GS} = -4.0 \text{ V}$ (4)  $V_{GS} = -5.0 \text{ V}$ 

 $(5) V_{GS} = -10.0 V$ 

Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = -200 \text{ mA}$ 

(1)  $T_j = 150 \, ^{\circ}C$ 

 $(2) T_{j} = 25 ^{\circ}C$ 

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 50 V, single P-channel Trench MOSFET

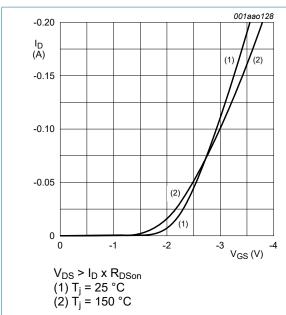
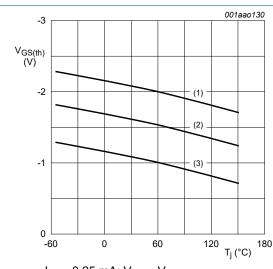


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature

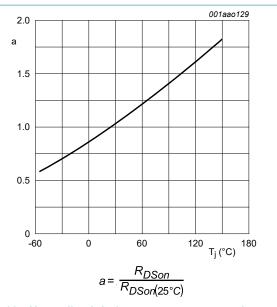
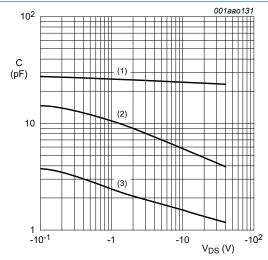


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $f = 1 MHz, V_{GS} = 0 V$ 

- $(1) C_{iss}$
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 50 V, single P-channel Trench MOSFET

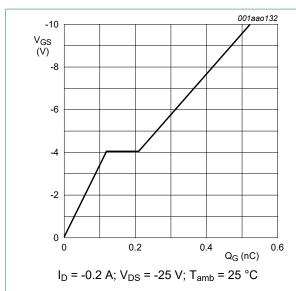


Fig. 15. Gate-source voltage as a function of gate charge; typical values

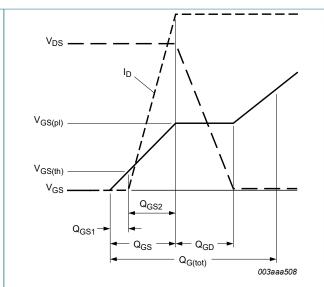
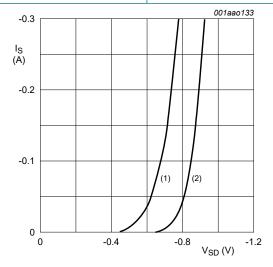


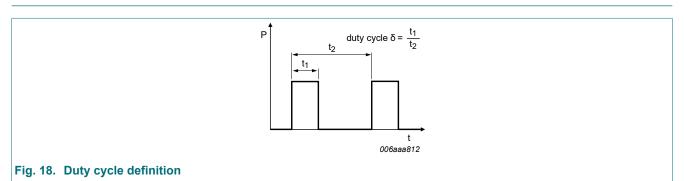
Fig. 16. Gate charge waveform definitions



 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ (2)  $T_j = 25 \,^{\circ}C$ 

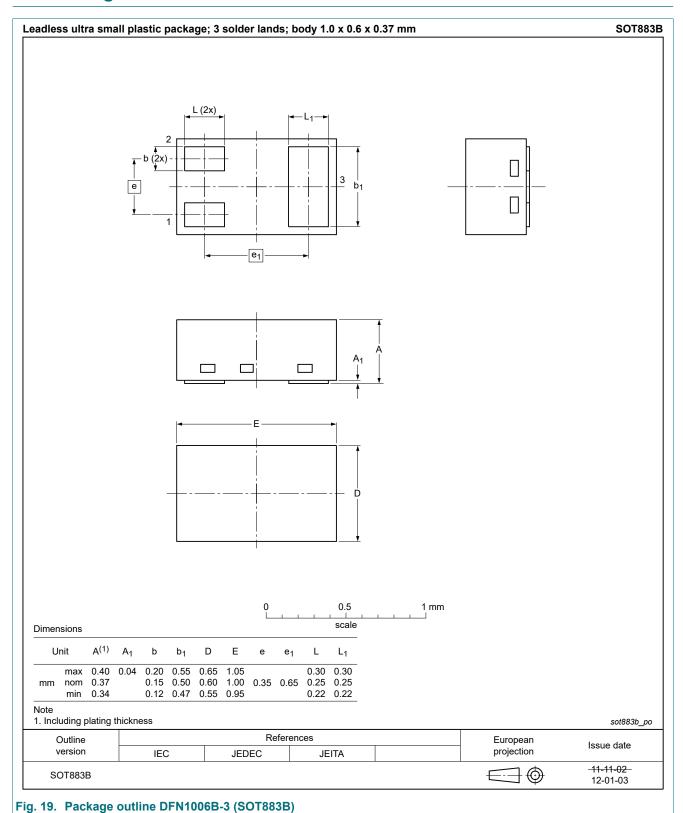
Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information



50 V, single P-channel Trench MOSFET

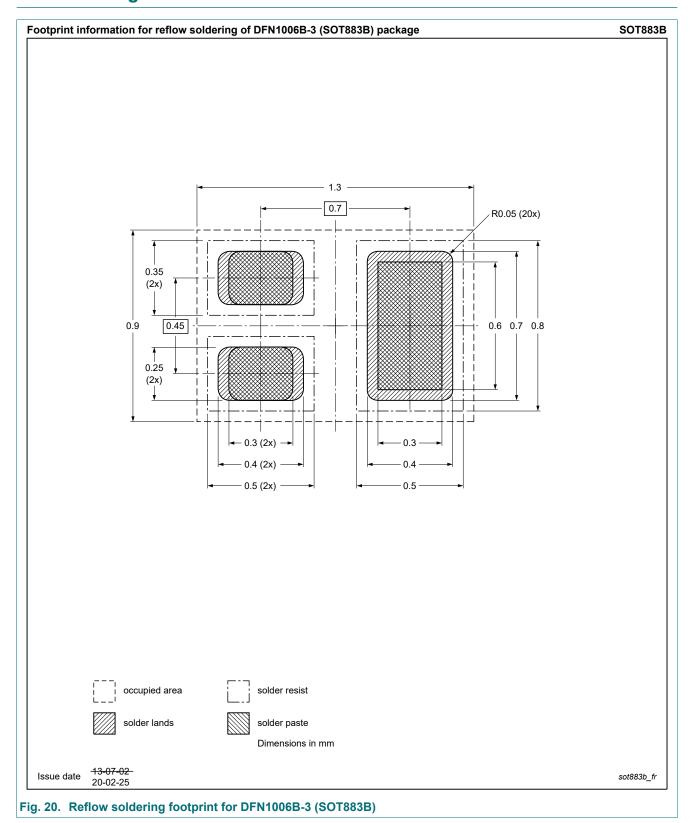
# 12. Package outline



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50 V, single P-channel Trench MOSFET

# 13. Soldering



## 50 V, single P-channel Trench MOSFET

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
BSS84AKMB v.2	20201027	Product data sheet	-	BSS84AKMB v.1				
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>							
BSS84AKMB v.1	20120606	Product data sheet	-	-				

### 50 V, single P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 50 V, single P-channel Trench MOSFET

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	Features and benefits

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